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## GENERAL TRANSMITTAL FORM UNDER 37 CFR 1.8 (LARGE ENTITY)

First Named Inventor	Chun Chen
Serial No.	10/636,173
Filing Date	August 7, 2003
Group Art Unit	2818
Examiner Name	Unknown
Confirmation No.	2105
Attorney Docket No.	400.234US01

Title: METHOD FOR PROGRAMMING AND ERASING AN NROM CELL

Mail Stop: AMENDMENT  
Commissioner for Patents  
P. O. Box 1450  
Alexandria, VA 22313-1450

### Enclosures

The following documents are enclosed:

Information Disclosure Statement (1 pg.); Form 1449 (7 pgs.); 58 copies of cited references; U.S. reference(s) not included pursuant to 37 C.F.R. 1.98 (c)(2)(i);  
 An itemized return-receipt postcard

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**Please charge any additional fees or credit any overpayments  
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**CUSTOMER NO. 27073**

### Submitted By

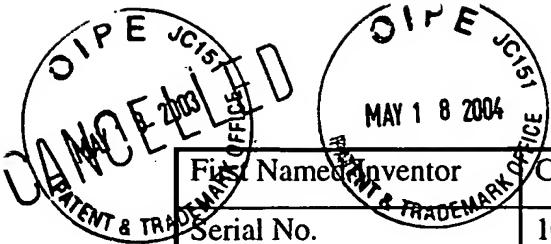
Name	Kenneth W. Bolvin	Reg. No.	34,125	Telephone	(612) 312-2211
Signature				Date	5/14/04

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Name	Rhonda L. Foley	Signature	
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(LARGE ENTITY TRANSMITTAL UNDER 37 CFR § 1.8)



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In compliance with 37 C.F.R. §§ 1.56 and 1.97, *et seq.*, the enclosed materials are brought to the attention of the Examiner for consideration in connection with the above-identified Application. Pursuant to 37 C.F.R. 1.98 (a)(2)(ik), as this application was filed after June 30, 2003, Applicant has not included copies of U.S. Patents or U.S. Patent Applications. Applicant respectfully requests that this Information Disclosure Statement be entered and the references listed on the attached Form 1449 be considered by the Examiner and made of record. Pursuant to MPEP §609, Applicant further requests that the Examiner initial next to each reference on the Form 1449 to indicate that the listed references have been considered. Applicant further requests that a copy of the initialed Form 1449 be returned with the next official communication.

As an Office Action has not yet issued in this application, Applicant believes that no fees are due. However, the Commissioner for Patents is hereby authorized to charge any additional fees to Deposit Account No. 501373. If the Examiner has any questions or concerns regarding this application, please contact the undersigned at (612) 312-2211.

Respectfully submitted,

Date: 5/14/04

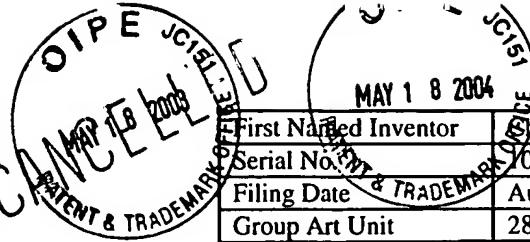
  
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## INFORMATION DISCLOSURE STATEMENT



MAY 18 2004

SC151

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**INFORMATION DISCLOSURE  
STATEMENT  
FORM PTO-1449**

Sheet 1 of 7

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